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PTO/SB/17 (12-04v2)
Approved for use through 7/31/2006. OMB 0651-0032
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the Paperwork Reduction Act of 1995, no person are required to respond to a collection of information unless it displays a valid OMB control number Complete if Known Effective on 12/08/2004. Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818). Patent#: 6.838.307 Application Number FEE TRANSMITTAL Issued: January 4, 2005 Filing Date Terry L. Gilton First Named Inventor For FY 2005 **Examiner Name** H. M. Lee Applicant claims small entity status. See 37 CFR 1.27 2823 Art Unit TOTAL AMOUNT OF PAYMENT M4065.1006/P1006-A 100.00 Attorney Docket No. METHOD OF PAYMENT (check all that apply) Check x Credit Card Money Order None Other (please identify): X Deposit Account Deposit Account Number: 04-1073 Deposit Account Name Dickstein Shapiro Morin & Oshinsky LLP For the above-identified deposit account, the Director is hereby authorized to: (check all that apply) Charge fee(s) indicated below Charge fee(s) indicated below, except for the filing fee Charge any additional fee(s) or underpayment of Credit any overpayments fee(s) under 37 CFR 1.16 and 1.17

#### **FEE CALCULATION** 1. BASIC FILING, SEARCH, AND EXAMINATION FEES **FILING FEES** SEARCH FEES **EXAMINATION FEES** Small Entity **Small Entity Small Entity Application Type** Fee (\$) Fee (\$) Fee (\$) Fee (\$) Fee (\$) Fees Paid (\$) Fee (\$) Utility 300 150 500 250 200 100 Design 200 100 100 50 130 65 Plant 200 100 300 150 160 80 Reissue 300 150 500 250 600 300 Provisional 200 100 0 2. EXCESS CLAIM FEES **Small Entity** Fee (\$) Fee Description Fee (\$) Each claim over 20 (including Reissues) 50 25 Each independent claim over 3 (including Reissues) 200 100 180

Multiple dependent claims

Total Claims

Extra Claims

x

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Multiple Dependent Claims

Fee (\$)

Fee Paid (\$)

Multiple Dependent Claims

Fee (\$)

Fee Paid (\$)

Indep. Claims

Extra Claims

Fee (\$)

Fee Paid (\$)

Extra Claims Fee (\$) Fee Paid (\$)

#### 3. APPLICATION SIZE FEE

If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).

Total Sheets Extra Sheets Number of each additional 50 or fraction thereof Fee (\$) = Fee Paid (\$)

- 100 = /50 (round up to a whole number) x = Fees Paid (\$)

4. OTHER FEE(S)

Non-English Specification, \$130 fee (no small entity discount)

Other (e.g., late filing surcharge): 1811 Certificate of correction 100.00

Signature

Registration No. (Altorney/Agent)

Name (Print/Type)

Registration No. (Altorney/Agent)

Date

September 30, 2005



Docket No.: M4065.1006/P1006-A

(PATENT)

#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:

Terry L. Gilton

Patent No.: 6,838,307

Issued: January 4, 2005

For: PROGRAMMABLE CONDUCTOR MEMORY

CELL STRUCTURE AND METHOD

THEREFOR

## REQUEST FOR CERTIFICATE OF CORRECTION PURSUANT TO 37 CFR 1.323

Attention: Certificate of Correction Branch

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

In the U.S. Patent Documents portion of References Cited the following 108 patent documents were omitted and should be included:

DOCUMENT	PUBLICATION	NAME OF PATENTEE
NUMBER	DATE	OR APPLICANT
TIG 6 6 70 6 10		
US 6,673,648	1/2004	Lowrey
US 2004/0035401	2/2004	Ramachandran et al.
US 2003/0212724	11/2003	Ovshinsky et al.
US 2003/0048744	3/2003	Ovshinsky et al.
US 2003/0212725	11/2003	Ovshinsky et al.
US RE 37,259E	7/2001	Ovshinsky
US 3,271,591	9/1966	Ovshinsky

DSMDB.1978822.1

US 3,961,314	6/1976	Klose et al.
US 3,966,317	6/1976	Wacks et al.
US 3,983,542	11/1976	Ovshinsky
US 3,988,720	10/1976	Ovshinsky
US 4,177,474	12/1979	Ovshinsky
US 4,267,261	5/1981	Hallman et al.
US 4,597,162	7/1986	Johnson et al.
US 4,608,296	8/1986	Keem et al.
US 4,637,895	1/1987	Ovshinsky et al.
US 4,646,266	2/1987	Ovshinsky et al.
US 4,664,939	5/1987	Ovshinsky
US 4,668,968	5/1987	Ovshinsky et al.
US 4,670,763	6/1987	Ovshinsky et al.
US 4,673,957	6/1987	Ovshinsky et al.
US 4,678,679	7/1987	Ovshinsky
US 4,696,758	9/1987	Ovshinsky et al.
US 4,698,234	10/1987	Ovshinsky et al.
US 4,710,899	12/1987	Young et al.
US 4,728,406	3/1988	Banerjee et al.
US 4,737,379	4/1988	Hudgens et al.
US 4,766,471	8/1988	Ovshinsky et al.
US 4,769,338	9/1988	Ovshinsky et al.
US 4,775,425	10/1988	Guha et al.
US 4,788,594	11/1988	Ovshinsky et al.
US 4,809,044	2/1989	Pryor et al.
US 4,818,717	4/1989	Johnson et al.
US 4,843,443	6/1989	Ovshinsky et al.
US 4,845,533	7/1989	Pryor et al.
US 4,853,785	8/1989	Ovshinsky et al.
US 4,891,330	1/1990	Guha et al.
US 5,128,099	7/1992	Strand et al.
US 5,159,661	10/1992	Ovshinsky et al.
US 5,166,758	11/1992	Ovshinsky et al.
US 5,177,567	1/1993	Klersy et al.
US 5,296,716	3/1994	Ovshinsky et al.
US 5,335,219	8/1994	Ovshinsky et al.
US 5,359,205	10/1994	Ovshinsky
US 5,341,328	8/1994	Ovshinsky et al.
US 5,406,509	4/1995	Ovshinsky et al.
US 5,414,271	5/1995	Ovshinsky et al.
US 5,534,711	7/1996	Ovshinsky et al.
US 5,534,712	7/1996	Ovshinsky et al.
US 5,536,947	7/1996	Klersy et al.

US 5,543,737	8/1996	Ovshinsky
US 5,591,501	1/1997	Ovshinsky et al.
US 5,596,522	1/1997	Ovshinsky et al.
US 5,687,112	11/1997	Ovshinsky
US 5,694,054	12/1997	Ovshinsky et al.
US 5,714,768	2/1998	Ovshinsky et al.
US 5,825,046	10/1998	Czubatyj et al.
US 5,912,839	6/1999	Ovshinsky et al.
US 5,933,365	8/1999	Klersy et al.
US 6,011,757	1/2000	Ovshinsky
US 6,087,674	7/2000	Ovshinsky et al.
US 6,141,241	10/2000	Ovshinsky et al.
US 6,339,544	1/2002	Chiang et al.
US 6,404,665	6/2002	Lowery et al.
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US 6,437,383	8/2002	Xu
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US 6,480,438	11/2002	Park
US 6,487,113	11/2002	Park et al.
US 6,501,111	12/2002	Lowery
US 6,507,061	1/2003	Hudgens et al.
US 6,511,862	1/2003	Hudgens et al.
US 6,511,867	1/2003	Lowery et al.
US 6,512,241	1/2003	Lai
US 6,514,805	2/2003	Xu et al.
US 6,531,373	3/2003	Gill et al.
US 6,534,781	3/2003	Dennison
US 6,545,287	4/2003	Chiang
US 6,545,907	4/2003	Lowery et al.
US 6,555,860	4/2003	Lowery et al.
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US 6,569,705	5/2003	Chiang et al.
US 6,570,784	5/2003	Lowery
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US 6,586,761	7/2003	Lowery
US 6,589,714	7/2003	Maimon et al.
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US 6,593,176	7/2003	Dennison
US 6,597,009	7/2003	Wicker
US 6,605,527	8/2003	Dennison et al.
US 6,613,604	9/2003	Maimon et al.

US 6,621,095	9/2003	Chiang et al.
US 6,625,054	9/2003	Lowery et al.
US 6,642,102	11/2003	Xu
US 6,646,297	11/2003	Dennison
US 6,649,928	11/2003	Dennison
US 6,667,900	12/2003	Lowery et al.
US 6,671,710	12/2003	Ovshinsky et al.
US 6,673,700	1/2004	Dennison et al.
US 6,674,115	1/2004	Hudgens et al.
US 6,687,427	2/2004	Ramalingam et al.
US 6,690,026	2/2004	Peterson
US 6,696,355	2/2004	Dennison
US 6,687,153	2/2004	Lowery
US 6,707,712	3/2004	Lowery
US 6,714,954	3/2004	Ovshinsky et al.

Attached Exhibit A includes copies of PTO Forms SB/08a listing these patent documents. Each document listed has been initialed as reviewed and accepted by the Examiner on 9/15/2004.

In the Foreign Patent Documents portion of References Cited the following reference contains a typographical error by the PTO to be corrected:

"WO WO 99/28194 6/1999" should read

--WO WO 99/28914 6/1999--.

In the Other Publications portion of References Cited the following references contain typographical errors by the PTO which should be corrected:

"Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilay r electrode, Thin Solid Films 131 (1985) L61-L64." Should read

--Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin Solid Films 131 (1985) L61-L64.--;

"Guin, J.-P.; Roux, I, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide galss s glass s below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269." Should read

- --Guin, J.-P.; Roux, I. T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.--;
- "Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G/Se glasses: clust ring f Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142." Should read
- --Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.--;
- "Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. L tt. 46 (1985) 543-545." Should read
- --Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. Lett. 46 (1985) 543-545.--;
- "McHardy et al., The dissolution of metals in am rphous chalcogenid s and the eff cts o electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f" Should read
- --McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)--;
- "Messoussi, R.; Berneda, J.C.; Benhide, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=N), i.Bi Mat. Chem. And Phys. 28 (1991) 253-258." Should read
- --Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258.--;
- "Popescu, C.; Croitoru, N., The contribution of the lateral thermal Instability to th switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537." Should read
- --Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.--;
- "Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphou s lenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73." Should read
- --Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.--;

"Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 48 B. Chem Soc. Japan, No. 12, pp. 3662-3365 (1973)." Should read

--Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 46 B, Chem. Soc. Japan, No. 12, pp. 3662-3365 (1973).--; and

"Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the |slope dTg/d<m>|at the rigidity percolation threshold (<m>x2.4), J. Non-Cryst. Solids 151 (1992) 149-154." Should read

--Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope |dTg/d<m>| at the rigidity percolation threshold (<m>x2.4), J. Non-Cryst. Solids 151 (1992) 149-154.--.

In the Specification the Applicant made the following errors:

Column 2, line 51, "and" should read --an--;

Column 6, line 2, "ovelying" should read --overlying--;

Column 6, line 58, "provide" should read --provided--; and

Column 6, line 60, "contining" should read --containing--.

The errors were made both by the PTO and found in the application as filed by applicant. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such corrections. Patentee respectfully solicits the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.1006/P1006-A.

Dated: September 30, 2005

Respectfully sabmitted,

Thomas J. D'Amico

Registration No.: 28,371

Peter McGee

Registration No.: 35,947

DICKSTEIN SHAPIRO MORIN & OSHINSKY

LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicant

# **Exhibit A**

PTC/SB/08a/b (08-03)

Approved for use through 07/31/2008. OMB 0851-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Progressive Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Sut	Sub-share Committee Commit			Complete If Known		
				Application Number	10/618,824-Conf. #5907	
	iformation	on dis	CLOSURE	Filing Date	July 14, 2003	
S	TATEMEN	T BY A	PPLICANT	First Named Inventor	Terry L. Gilton	
	(1104 00 mm)			Art Unit	NA 2823	
	(Use as many sheets as necessary)			Examiner Name	Not Yot Assigned H. Lee	
Sheet	1	of	1	Attorney Docket Number	M4065.1006/P1006-A	

U.S. PATENT DOCUMENTS						
Examiner	Cite	Document Number	Publication Data	Name of Datasta	Pages, Columns, Lines, Where	
Initiats*	No.	Number-Kind Code <sup>2</sup> (# Imown)	MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Relevant Passages or Relevant Figures Appear	
11	AA	US-6,673,648	01/06/2004	Lowrey		

	FOREIGN PATENT DOCUMENTS							
Examiner	Cite	Foreign Patent Document	Publication	Name of Patentee or	Pages, Columns, Lines,			
Initials*		Country Code®-Humber®-Kind Code® (# Isrown)	MM-00-7777	Applicant of Cited Danier	Where Relevant Passages or Relevant Figures Appear	T⁰		
						$\vdash$		

"EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Dry line thingth citation seems complimence and not considered, include copy of this form with next communication to applicant. "Applicant's unique citation designation tumber (optional)." SM (Ands Codes of USPTO Patent Documents at www.uspip.gov or MPEP 901.04. "Enter Office that issued the document, by the two-lease-code WIPO Standard ST.3). "For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. "Vind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible." Applicant is to place a check mark here if English language

NON PATENT LITERATURE DOCUMENTS						
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), little of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²			

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not cliation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Bei Min Lu

<sup>&</sup>lt;sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.



PTO/SB/08a/b (08-03)
Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Timdemark Office; U.S. DEPARTMENT OF COMMERCE

Substitut	is for form 1448A	/B/PTO		Complete If Known		
				Application Number	10/618,824	
INF	ORMATI	ON DISC	LOSURE	Filing Date	July 14, 2003	
STA	TEMEN	T BY API	PLICANT	First Named Inventor	Terry L. Gilton	
	***			Art Unit	2823	
	(Use as man	y sheets as nec	ssary)	Examiner Name	Hsien Ming Lee	
Sheet	1	of	3	Attorney Docket Number	M4065.1006/P1006-A	

			U.S. PA	TENT DOCUMENTS	
Examiner Initiats	Cite No.1	Document Number  Number-Kind Code <sup>2</sup> ( # known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
100	A	US 2004/0035401	2/2004	Ramachandran et al.	Leftmas Abbers.
THE STATE OF THE S	В	US 2003/0212724	11/2003	Ovshinsky et al.	
<del></del>	c	US 2003/0048744	3/2003	Ovshinsky et al.	
	<del>lŏ</del>	US 2003/0212725	11/2003	Ovshinsky et al.	
	Ē	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,961,314	6/1976	Klose et al.	
	H	US 3,966,317	6/1976	Wacks et al.	
	1	US 3,983,542	11/1976	Ovshinsky	
	J	US 3,988,720	10/1976	Ovshinsky ( )	
	ĸ	US 4,177,474	12/1979	Ovshinsky	<del>  }/                                   </del>
	L	US 4,267,261	5/1981	Hallman et al.	<b>U</b>
	M	US 4,597,162	7/1986	Johnson et al.	
	N	US 4,608,296	8/1986	Keem et al.	
	lo	US 4,637,895	1/1987	Ovshinsky et al.	
	ΙĎ	US 4.646.266	2/1987	Ovshinsky et al.	
	la	US 4,664,939	5/1987	Ovshinsky	
	Ŕ	US 4,668,968	5/1987	Ovshinsky et al.	
	s	US 4,670,763	6/1987	Ovshinsky et al.	
	Ť	US 4,673,957	6/1987	Ovshinsky et al.	
	Ù	US 4,678,679	7/1987	Ovshinsky	
	V	US 4.696.758	9/1987	Ovshinsky et al.	
_	ŵ	US 4,698,234	10/1987	Ovshinsky et al.	
	X	US 4,710,899	12/1987	Young et al.	
	Ŷ	US 4,728,406	3/1988	Banerjee et al.	
_	Ż	US 4,737,379	4/1988	Hudgens et al.	
	Ā1	US 4,766,471	8/1988	Ovshinsky et al.	
	B1	US 4,769,338	9/1988	Ovshinsky et al.	
	Ci	US 4,775,425	10/1988	Guha et al.	
	D1	US 4,788,594	11/1988	Ovshinsky et al.	
<del></del>	E1	US 4,809,044	2/1989	Pryor et al.	· · · · · · · · · · · · · · · · · · ·
	Fi	US 4.818.717	4/1989	Johnson et al.	
	G1	US 4,843,443	6/1989	Ovshinsky et al.	
	Hi	US 4,845,533	7/1989	Pryor et al.	
	11	US 4,853,785	8/1989	Ovshinsky et al.	
	<del>]</del> 1	US 4,891,330	1/1990	Guha et al.	
	K1	US 5,128,099	7/1992	Strand et al.	
	L1	US 5,159,681	10/1992	Ovshinsky et al.	
	M1	US 5,166,758	11/1992		
<del>   -  </del>	N1	US 5,166,756		Ovshinsky et al. Klersy et al.	
	01	US 5,296,716	3/1994		
	P1	US 5,335,219		Ovshinsky et al.	
	6	US 5,335,219 US 5,359,205		Ovshinsky et al.	
	RI.		10/1994	Ovshinsky	
	SI			Ovshinsky et al.	
+	سرو	US 5,406,509	4/1995	Ovshinsky et al.	

PTO/SB/08a/b (08-03)
Approved for use through 07/31/2008. OMB 0851-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE spond to a collection of information unless it contains a valid OMB contrain a refer

Sub	stitute for form 1449A/B	/PTO		Completo If Known		
				Application Number	10/618,824	
II.	IFORMATIC	ON DISC	LOSURE	Filing Date	July 14, 2003	
S	<b>TATEMENT</b>	BY AP	PLICANT	First Named Inventor	Terry L. Gilton	
				Art Unit	2823	
	(Use as many	shèets as nec	essary)	Examiner Name	Hsien Ming Lee	
Sheet	2	of	3	Attorney Docket Number	M4065.1006/P1006-A	

0	Ti	US 5,414,271	5/1995	Ovshinsky et al.	<u> </u>
7次	Üİ	US 5,534,711	7/1996	Ovshinsky et al.	
<u> </u>	Vi	US 5,534,712	7/1996	Ovshinsky et al.	
	W1	US 5,536,947	7/1996	Klersy et al.	
<del></del>	Xi	US 5,543,737	8/1996	Ovshinsky	
<del></del>	<del> Ŷi</del>	US:5,591,501	1/1997	Ovshinsky et al.	
<del>                                     </del>	Ž1	US 5,596,522	1/1997	Ovshinsky et al.	
l	A2	US 5,687,112	11/1997	Ovshinsky	
<del></del>	B2	US 5,694,054	12/1997	Ovshinsky et al.	
<del>                                     </del>	C2	US 5,714,768	2/1998	Ovshinsky et al.	
<del>  </del>	D2	US 5,825,046	10/1998	Czubatyj et al.	
<del>                                     </del>	E2	US 5,912,839	6/1999	Ovshinsky et al.	755
	F2	US 5,933,365	8/1999	Klersy et al.	HD)\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
<del>                                     </del>	G2	US 6,011,757	1/2000	Ovshinsky	
<del></del>	H2	US 6,087,674	7/2000	Ovshinsky et al.	<del>                                    </del>
<del></del>	12	US 6,141,241	10/2000	Ovshinsky et al.	<del></del>
<del>                                     </del>	J2	US 6,339,544	1/2002	Chlang et al.	
<del>                                     </del>	K2	US 6,404,665	6/2002	Lowery et al.	
	12	US 6,429,064	8/2002	Wicker	
	M2	US 6,437,383	8/2002	Xu	
<b></b>	N2	US 6,462,984	10/2002	Xu et al.	
	02	US 6,480,438	11/2002	Park	
	P2	US 6,487,113	11/2002	Park et al.	
	02	US 6,501,111	12/2002	Lowery	
	R2	US 6,507,061	1/2003	Hudgens et al.	
	S2	US 6,511,862	1/2003	Hudgens et al.	
	T2	US 6,511,867	1/2003	Lowery et al.	
	U2	US 6,512,241	1/2003	Lai	
	V2	US 6,514,805	2/2003	Xu et al.	
	W2	US 6,531,373	3/2003	Gill et al.	
	X2	US 6,534,781	3/2003	Dennison	
	Y2	US 6,545,287	4/2003	Chlang	
	Z2	US 6,545,907	4/2003	Lowery et al.	
	A3	US 6,555,860	4/2003	Lowery et al.	
	<b>B3</b>	US 6,563,164	5/2003	Lowery et al.	
	СЗ	US 6,566,700	5/2003	Xu	
	D3	US 6,567,293	5/2003	Lowery et al.	
	E3	US 6,569,705	5/2003	Chlang et al.	
	F3	US 6,570,784	5/2003	Lowery	
	G3	US 6,576,921	6/2003	Lowery	
	НЗ	US 6,586,761	7/2003	Lowery	
	13	US 6,589,714	7/2003	Malmon et al.	
	J3	US 6,590,807	7/2003	Lowery	
	КЗ	US 6,593,176	7/2003	Dennison	
	L3	US 6,597,009	7/2003	Wicker	
	МЗ	US 6,605,527	8/2003	Dennison et al.	
	N3	US 6,613,604	9/2003	Malmon et al.	
	<b>O3</b>	US 6,621,095	9/2003	Chlang et al.	
	P3	US 6,625,054	9/2003	Lowery et al.	
10	Qβ	US 6,642,102	11/2003	Xu	
7		<del></del>			

PTO/SB/08a/b (08-03)

Approved for use through 07/31/2008, OMB 0851-0031
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				Application Number	10/618,824	
11	<b>IFORMATIC</b>	ON DISC	LOSURE	Filing Date	July 14, 2003	
S	TATEMENT	BY AP	PLICANT	First Named Inventor	Terry L. Gilton	
			_	Art Unit	2823	
	(Use as many sheets as necessary)			Examiner Name	Hsien Ming Lee	
Sheet	et 3 of 3		Attorney Docket Number	M4065.1006/P1008-A		

Th	R3	US 6,646,297	11/2003	Dennison
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	Т3	US 6,667,900	12/2003	Lowery et al.
	U3	US 6,671,710	12/2003	Ovshinsky et al.
	V3	US 6,673,700	1/2004	Dennison et al.
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	Y3	US 6,690,026	2/2004	Peterson
	<b>Z3</b>	US 6,696,355	2/2004	Dennison Co -
	A4	US 6,687,153	2/2004	Lowery (( (( )))
	B4	US 6,707,712	3/2004	Lowery
7	C4	US 6,714,954	3/2004	Ovshinsky et al.

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Examiner Initials*	Cite No.1	Foreign Patent Document  Country Code <sup>3</sup> (Number <sup>4</sup> +Kind Code <sup>5</sup> (# Innown)	Publication Date -MMFDD-YYYY	Name of Patentse or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	70	

"EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). See Kinds Codes of USPTO Patent Documents at <a href="https://www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. Mind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. Applicant is to place a check mark here if English tanguage Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²		

<sup>.\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Drew line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1779924 v1; 125#C011,DOC

Low Ming Lee

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### UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

Page <u>1</u> of <u>5</u>

PATENT NO.

6,838,307

APPLICATION NO. :

10/618,824

**ISSUE DATE** 

January 4, 2005

INVENTOR(S)

Terry L. Gilton

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the U.S. Patent Documents portion of References Cited the following 108 patents were omitted and should be included:

DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT
US 6,673,648 US 2004/0035401 US 2003/0212724 US 2003/0048744 US 2003/0212725 US RE 37,259E US 3,271,591 US 3,961,314 US 3,966,317 US 3,983,542 US 3,988,720 US 4,177,474 US 4,267,261 US 4,597,162 US 4,608,296 US 4,637,895 US 4,646,266	1/2004 2/2004 11/2003 3/2003 11/2003 7/2001 9/1966 6/1976 6/1976 11/1976 10/1976 12/1979 5/1981 7/1986 8/1986 1/1987 2/1987	Lowrey Ramachandran et al. Ovshinsky et al. Ovshinsky et al. Ovshinsky Ovshinsky Klose et al. Wacks et al. Ovshinsky Ovshinsky Ovshinsky Ovshinsky Ovshinsky Ovshinsky Ovshinsky Ovshinsky Hallman et al. Johnson et al. Keem et al. Ovshinsky et al.

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Older the Paperwork Reduction	m Act of 1995, no persons are required to r	espond to a collection of information unless it	(Also Form PTO-1050)
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		everimenty of all	
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'WO WO 99/28194	6/1999" should r	ead	

--WO

WO 99/28914

6/1999--.

In the Other Publications portion of References Cited these typographical errors need corrections:

MAILING ADDRESS OF SENDER (Please do not use customer number below): Thomas J. D'Amico DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 3 2101 L Street NW Washington, DC 20037-1526

- "Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilay r electrode, Thin Solid Films 131 (1985) L61-L64." Should read
- --Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin Solid Films 131 (1985) L61-L64.--;
- "Guin, J.-P.; Roux, I, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide galss s glass s below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269." Should read
- --Guin, J.-P.; Roux, I. T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.--;
- "Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G /Se glasses: clust ring f Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142." Should read
- --lyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.--;
- "Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. L tt. 46 (1985) 543-545." Should read
- --Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. Lett. 46 (1985) 543-545.--;
- "McHardy et al., The dissolution of metals in am rphous chalcogenid s and the eff cts o electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f' Should read
- --McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)--;
- "Messoussi, R.; Berneda, J.C.; Benhide, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=N), i.Bi Mat. Chem. And Phys. 28 (1991) 253-258." Should read
- --Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258.--;
- "Popescu, C.; Croitoru, N., The contribution of the lateral thermal Instability to th switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537." Should read
- --Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.--:
- "Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphou s lenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73." Should read
- --Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.--;

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"Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 48 B. Chem Soc. Japan, No. 12, pp. 3662-3365 (1973)." Should read

--Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 46 B, Chem. Soc. Japan, No. 12, pp. 3662-3365 (1973).--; and

"Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope dTg/d<m>|at the rigidity percolation threshold (<m>x2.4), J. Non-Cryst. Solids 151 (1992) 149-154." Should read

--Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope |dTg/d<m>| at the rigidity percolation threshold (<m>x2.4), J. Non-Cryst. Solids 151 (1992) 149-154.--.

In the Specification the Applicant made the following errors:

Column 2, line 51, "and" should read --an--;

Column 6, line 2, "ovelying" should read --overlying--;

Column 6, line 58, "provide" should read --provided --; and

Column 6, line 60, "contining" should read --containing--.

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